Hex 3-State Noninverting Buffer with Separate 2-Bit and 4-Bit Sections

High-Performance Silicon-Gate CMOS

The MC74HC367A is identical in pinout to the LS367. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device is arranged into 2-bit and 4-bit sections, each having its own active-low Output Enable. When either of the enables is high, the affected buffer outputs are placed into high-impedance states. The HC367A has noninverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- These are Pb-Free Devices

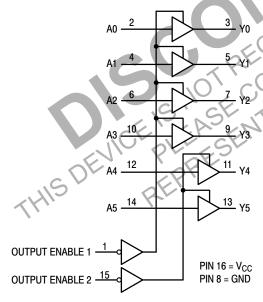
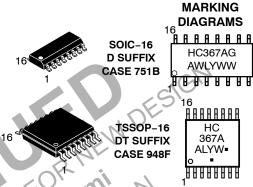


Figure 1. Logic Diagram



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A = Assembly Location

VL, L = Wafer Lot YY, Y = Year

WW, W = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

OUTPUT (1 •	16	v _{cc}
A0 [2	15	OUTPUT ENABLE 2
Y0 [3	14] A5
A1 [4	13] Y5
Y1 [5	12	A4
A2 [6	11	Y4
Y2 [7	10] A3
GND [8	9] Y3

FUNCTION TABLE

Inpu	ıts	Output
Enable 1, Enable 2	Α	Υ
L	L	L
L	Н	Н
Н	X	Z

X = don't care Z = high impedance

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	٧
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	٧
I _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, SOIC Package TSSOP Package		mW
T _{stg}	Storage Temperature	-65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

T _{stg}	Storage Temperature	-65 to +	150	°C	Unused outputs must be leπ open.
ratings only Extended e reliability.	xceeding Maximum Ratings may damage the device. Ma x. Functional operation above the Recommended Operating xposure to stresses above the Recommended Operating C	g Conditio	ns is no	implied	l.
Symbol	Parameter	Min	Max	Unit	N
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	NE
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	V	1 1
T _A	Operating Temperature, All Package Types	-55	+125	°C	cention.
t _r , t _f	Input Rise and Fall Time $ \begin{array}{c} \text{V}_{CC} = 2.0 \text{ V} \\ \text{(Figure 2)} \end{array} $ $ \begin{array}{c} \text{V}_{CC} = 3.0 \text{ V} \\ \text{V}_{CC} = 4.5 \text{ V} \\ \text{V}_{CC} = 6.0 \text{ V} \end{array} $	0 0 0	1000 600 500 400	ns	ORNATION ORNALION
	(Figure 2) V _{CC} = 3.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	AC YEF	OR		

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

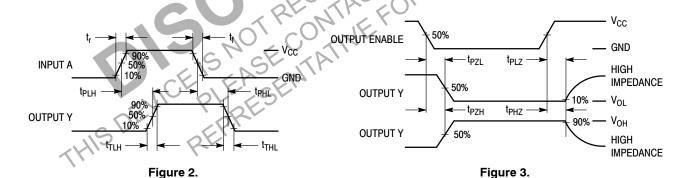
				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\label{eq:Vin} \begin{array}{ll} V_{in} = V_{IH} & \qquad & I_{out} \leq 3.6 \; \text{mA} \\ & I_{out} \leq 6.0 \; \text{mA} \\ & I_{out} \leq 7.8 \; \text{mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\label{eq:vin} \begin{array}{ll} V_{in} = V_{IL} & I_{out} \leq 3.6 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{array}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	±0.1	±1.0	± 1.0	μΑ
l _{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	±0.5	± 5.0	± 10	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4	40	160	μΑ
~ \	Maximum Quiescent Supply Current (per Package)	SENTATIVE FOR					

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

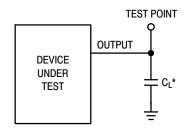
			Gu	aranteed Li		
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	120 60 24 20	150 75 30 26	180 90 36 31	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	175 90 35 30	220 110 44 37	265 135 53 45	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	190 95 38 32	240 120 48 21	285 150 57 48	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)		15	15	15	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Buffer)	EAL 18 211 60	pF

SWITCHING WAVEFORMS



TEST CIRCUITS



DEVICE UNDER TEST C_{L^*} TEST POINT

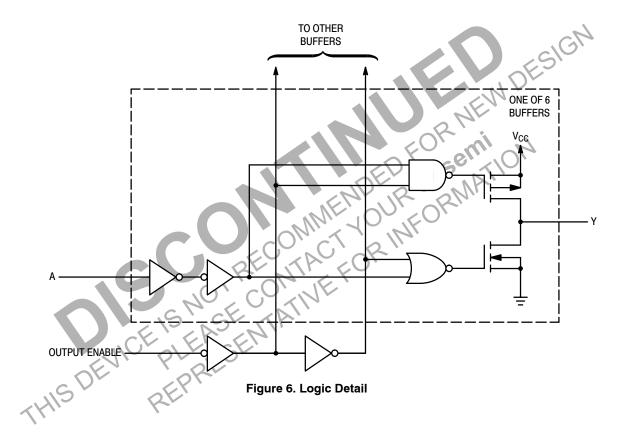
OUTPUT

1 k Ω CONNECT TO V_{CC} WHEN TESTING t_{PLZ} AND t_{PZL} . CONNECT TO GND WHEN TESTING t_{PHZ} AND t_{PZH} .

*Includes all probe and jig capacitance

Figure 4.

Figure 5.



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC367ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC367ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74HC367ADTG	TSSOP-16 (Pb-Free)	96 Units / Tube
MC74HC367ADTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Includes all probe and jig capacitance



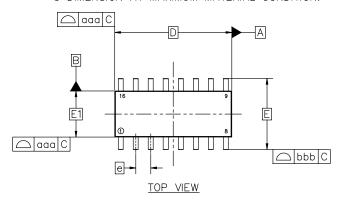


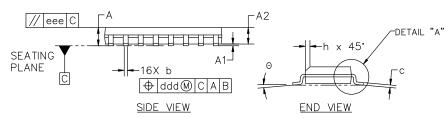
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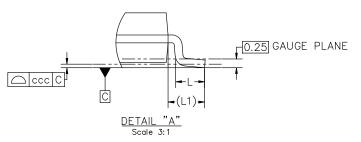
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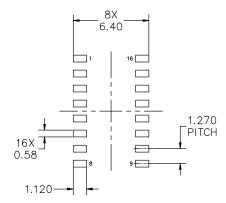
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS						
DIM	MIN	NOM	MAX			
А	1.35	1.55	1.75			
A1	0.10	0.18	0.25			
A2	1.25	1.37	1.50			
b	0.35	0.42	0.49			
С	0.19	0.22	0.25			
D		9.90 BSC				
Е	6.00 BSC					
E1	3.90 BSC					
е	1.27 BSC					
h	0.25		0.50			
L	0.40	0.83	1.25			
L1		1.05 REF				
Θ	0.		7*			
TOLERAN	CE OF FO	RM AND	POSITION			
aaa		0.10				
bbb	0.20					
ccc		0.10				
ddd		0.25				
eee		0.10				



RECOMMENDED MOUNTING FOOTPRINT

*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D

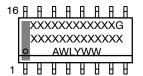
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DATE 18 OCT 2024

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

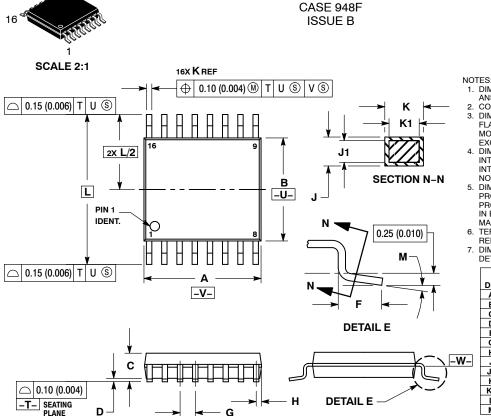
STYLE 1:		STYLE 2:		STYLE 3:	S	STYLE 4:	
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.		11.	
	EMITTER	12.	CATHODE	12.		12.	
13.		13.	CATHODE	13.	COLLECTOR, #4	13.	
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	
	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
STYLE 5: PIN 1.	DRAIN, DYE #1	STYLE 6: PIN 1.		STYLE 7: PIN 1.	SOURCE N-CH		
	DRAIN, #1	PIN 1. 2.	CATHODE	PIN 1. 2.	COMMON DRAIN (OUTPUT)		
PIN 1.	DRAIN, #1 DRAIN, #2	PIN 1. 2. 3.	CATHODE CATHODE	PIN 1.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2.	DRAIN, #1 DRAIN, #2 DRAIN, #2	PIN 1. 2. 3. 4.	CATHODE CATHODE CATHODE	PIN 1. 2.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH		
PIN 1. 2. 3.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4	PIN 1. 2. 3. 4. 5. 6.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5. 6.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4	PIN 1. 2. 3. 4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5. 6. 7.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4 GATE, #4 GATE, #3	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 SOURCE, #2 SOURCE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 SOURCE, #2 SOURCE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		

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DATE 19 OCT 2006



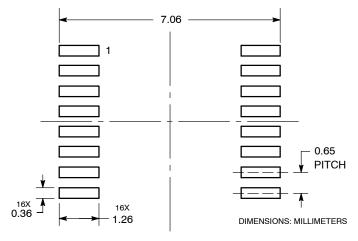


TSSOP-16 WB

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ĺ	6.40 BSC		0.252 BSC	
M	0 °	8°	0°	8 °

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TSSOP-16		PAGE 1 OF 1	

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